

5 modifications, and equivalents as may be included within the spirit and scope of
the invention as defined by the appended claims.

CLAIMS

10 What is claimed is:

1. A Machine for Production of Granular Silicon comprising:

a heating section located below a reacting section; where said
heating section can consist of one or more tubes heated by one or more heaters

15 a mechanism that pulses granules back and forth between the
heating and reacting sections ;

separate injection of silicon containing gases and non silicon
containing gases;

heating the non silicon containing gases above the reaction
20 temperature;

cooling each injection location of the silicon containing gases;

2. a machine of claim 1 where there are multiple stages each one
consisting of a heater and reaction section; where each reactor section has one
or more injection nozzles for gases which promote additional reaction, in the
25 silane reactor the gas to the reaction section would be silane, for the
hydrohalosilane, e.g. trichlorosilane or tribromosilane, reactor the gas to the
reactor section could be the hydrohalosilane alone, hydrogen alone or a
combination of the two

3. a machine of claim 1 or 2 which recovers heat from granules by direct
30 contact with a high purity non silicon depositing or reacting gases: such gases

5 can be hydrogen, helium, argon, nitrogen, silicon tetrachloride and silicon tetrabromide and must be low in carbon and oxygen containing contaminants, such as oxygen, water, carbon monoxide, carbon dioxide and methane, which contaminants must be below 1 ppmwt and preferably below 10ppbwt. Gases such as silicon trichlorosilane and silane are not usable because they

10 decompose, hydrogen chloride, hydrogen bromide or mixtures of gases, which react such as a silicon tetrachloride, and hydrogen mixture are not usable because they can react with the granules

4. a heat exchanger in which silicon containing gases are heated by hot liquid or condensing vapor maintained within a temperature range which cannot cause decomposition of the gases ;which temperature range is typically between 200-400 C but more particularly between 300-350 C

15 5. a sieving device by which silicon granules are sieved using one or more sieves manufactured from non contaminating sieve material and undersized granules returned to reactor ; where the noncontaminating sieve material is selected from materials which contain silicon such as single crystal silicon, polycrystalline silicon, silicon oxide, silicon nitride, silicon oxynitride and silicon carbide and where the abradable surfaces are low in contaminants such as boron, phosphorus, aluminum, arsenic, iron, copper and other metals, such contaminants will typically be below 1000 ppmwt and preferably below 100

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25 ppmwt

6. an optional feedstock recovery section; where a silicon quadrahalide such as silicon tetrachloride or silicon tetrabromide is injected, mixed with the reactor effluent then quenched at an optimal temperature to recover the silicon hydrohalides such as trichlorosilane and dichlorosilane

5 7. one or more cooled joints between external equipment and the reactor
which transmit hot gases or solids. and which are cooled using localized, one or
more, microchannels positioned to primarily cool the elastomeric O-ring to a
temperature such that decomposition of the O-ring or increased permeability of
the o-ring to oxygen ,water and carbon dioxide does not cause significant
10 contamination without excessive heat loss , such temperature is typically 25-300
C and preferably 50-150 C for o-rings made from high purity fluorocarbon o-rings
such as Viton, Kalrez and Teflon

15 8. a machine of claim one or two where there is external flow control of
each injection point, such flow control may be direct with flow control of each
nozzle done independently, indirect by means of a flow distribution device such
as a manifold or a combination of the two where some nozzles are ganged in
groups

20 9. a machine of claim 8 where the shape of the pulse and/or the
distribution of flow between nozzles may be adjusted to control the generation of
new particles without changing the total flow

10 10. a preferred variation of claim 8 where the flow of gas to each nozzle is
controlled before the heater/s and an even more preferred option where multiple
separate flows are heated in the same heater

25 11. a preferred combination of the above claims for the use of silane as a
feedstock, where there are; two or more stages; high purity hydrogen is used for
the non silicon containing gas to the first heating section, for the cooling of the
granular silicon and for return of undersize granules to the reactor; the sieving
device is made from high purity quartz tubes and polycrystalline silicon sieves,
the feedstock recovery system is not used; cooled joints are used for all the inlets
30 and outlets of the reactor; the silane heat exchanger uses a condensing vapor

5 maintained in the temperature range 340-360 C and each gas injection location
is independently controlled.

12. a preferred combination of the above claims for the use of
trichlorosilane and/or dichlorosilane as a feedstock, where there are; two or more
stages; high purity hydrogen is used for the non silicon containing gas to the first
10 heating section and to the second reacting section, for the cooling of the granular
silicon and for return of undersize granules to the reactor; the sieving device is
made from high purity quartz tubes and polycrystalline silicon sieves, the
feedstock recovery system is used and silicon tetrachloride is injected to cool the
effluent from 1100 C to 900 C and recover hydrohalosilanes for recycle ; cooled
15 joints are used for all the inlets and outlets of the reactor; the chlorosilane heat
exchanger uses a condensing vapor maintained in the temperature range 340-
360 C and each gas injection location is independently controlled

13. a variation of claim 1,2,11 or 12 where the heater section is of smaller
diameter than the reactor section above it and connected by a tapered section,
angle of said tapered section to be between 10 and 80 degrees from the vertical
20 and preferably between 30-60 degrees from the vertical

14. a variation of claims 1,2,11,12 and 13 where the heaters used in the
heating sections may be resistance heaters, inductive RF heaters, microwave
heaters, lamp heaters or lasers but are preferably resistance heaters

25 15. a further variation of claims 1,2,11,12 and 13 where a high efficiency
cyclone is used to remove dust from the effluent gases and to provide residence
time for the feedstock recovery system when this is used

30 16. a yet further variation of claims 1,2,11,12 and 13 where a silicon
etching gas or mixture of gases may be injected through one or more nozzles for
the purpose of etching wall deposits from all or part of the reactor, such gases

5 may be elemental halides such as chlorine or bromine, hydrogen halides such as hydrogen chloride or hydrogen bromide or combinations of hydrogen and silicon tetrahalides such as silicon tetrachloride or silicon tetrabromide

17. a additional improvement to the above claims where the reactor is supported upon a weigh cell, capable of weighing the reactor and contents and
10 measuring the intermittent force exerted by the pulsing gas and the connections to and from the reactor are flexible enough to allow the slight deflection required by the weigh cell, said deflection to be less than 1mm and preferably less than 0.5mm, and the thermal expansion of the reactor relative to the support structure, said thermal expansion to be less than 1" (25mm) and preferably less than 1/4"
(6mm)

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18. a further variation on the above claims where all or a portion of the non silicon containing gases are heated to a temperature below the reaction temperature outside the heating section then heated to a temperature above the reactor temperature inside the heater prior to entry to the reactor section

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19. a yet further variation of claims 12 and 13 where the second stage heater section does contain some residual silicon dust or silicon containing gases from the first stage reactor section that can form a wall deposit

20. a variation of claim 5 where the sieving and return of undersize granules is done on a batch basis